









**DRV8846** 

#### SLLSEK2A - JUNE 2014-REVISED MARCH 2017

# **DRV8846 Dual H-Bridge Stepper Motor Driver**

#### **Features**

- **PWM Microstepping Motor Driver** 
  - Built-In Microstepping Indexer
  - Up to 1/32 Microstepping
  - Step/Direction Control
- Multiple Decay Modes
  - Smart tune Technology
  - Mixed Decay
  - Slow Decay
  - Fast Decay
- Configurable Off-Time PWM Chopping
  - 10-, 20-, or 30-μs Off-Time
- Adaptive Blanking Time for Smooth Stepping
- 4- to 18-V Operating Supply Voltage Range
- 1.4-A (Full Scale (Max Drive) Current per H-Bridge (at 25°C)
- Low-Current Sleep Mode
- 3-Bit Torque DAC to Scale Motor Current
- Thermally Enhanced Surface Mount Package
- **Protection Features** 
  - VM Undervoltage Lockout (UVLO)
  - Overcurrent Protection (OCP)
  - Thermal Shutdown (TSD)
  - Fault Condition Indication Pin (nFAULT)

# Applications

- **Printers**
- Scanners
- Video Security Cameras
- **Projectors**

## 3 Description

The DRV8846 provides a highly-integrated stepper motor driver for cameras, printers, projectors, and other automated equipment applications. The device has two H-bridges and a microstepping indexer and is intended to drive a bipolar stepper motor. The output block of each H-bridge driver consists of Nchannel and P-channel power MOSFETs configured as full H-bridges to drive the motor windings. The DRV8846 is capable of driving up to 1.4-A full-scale output current (with proper heatsinking and  $T_A$  = 25°C).

A simple STEP/DIR interface allows easy interfacing to controller circuits. Pins allow configuration of the motor in full-step up to 1/32-step modes. Decay mode is configurable so that smart tune, slow decay, fast decay, and mixed decay can be used. The PWM current chopping off-time can also be selected. A lowpower sleep mode is provided which shuts down internal circuitry to achieve very-low quiescent current draw. This sleep mode can be set using a dedicated nSLEEP pin.

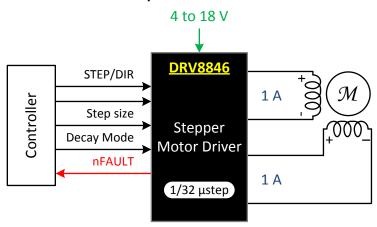
Internal protection functions are provided for UVLO, overcurrent protection, short circuit protection, and overtemperature. Fault conditions are indicated via a nFAULT pin.

### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
DRV8846	VQFN (24)	4.00 × 4.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### Simplified Schematic





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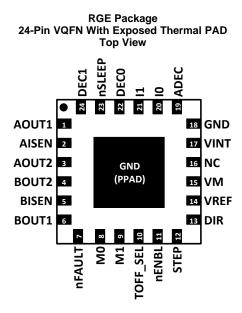
# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Original (June 2014) to Revision A	Page
•	Changed references of adaptive decay to smart tune	1
•	Updated Description	1
•	Changed Handling Ratings table to an ESD Ratings table and moved T <sub>stq</sub> to Absolute Maximum Ratings	4
•	Changed references of rms current to full-scale current and changed the maximum current from 1 to 1.4 A throughout the document	4
•	Updated the R <sub>DS(ON)</sub> units and V <sub>HYS</sub> in the <i>Electrical Characteristics</i>	5
•	Changed changed the nENBL setting from 0 to 1 in the Micro-Stepping Indexer section	10
•	Added more information regarding the ADEC pin	18
•	Updated the Device Functional Modes	21
•	Added the Documentation Support, Receiving Notification of Documentation Updates, and Community Resources sections	26



# 5 Pin Configuration and Functions



**Pin Functions** 

P	PIN	1/0	DESCRIPTION			
NAME	NO.	I/O		DESCRIPTION		
ADEC	19	I	Smart tune enable	Logic low sets decay modes by DEC0 and DEC1 pins; logic high – smart tune operation is enabled; must be set prior to coming out of sleep; internal pulldown		
AISEN	2	0	Winding A sense	Connect to current sense resistor for bridge A, or GND if current regulation is not required		
AOUT1	1	0	Minding A quitaut			
AOUT2	3	U	Winding A output			
BISEN	5	0	Winding B sense	Connect to current sense resistor for bridge B, or GND if current regulation is not required		
BOUT1	6	0	Winding Doutnut			
BOUT2	4	U	Winding B output			
DEC0	22	I	Decay mode setting pins	Sets the decay mode; see description section; tri-level pin		
DEC1	24	I	Decay mode setting pins	Sets the decay mode, see description section, thriever pin		
DIR	13	I	Direction input	Logic level sets the direction of stepping; internal pulldown		
GND	18, PPAD	PWR	Device ground	Both the GND pin and device thermal pad must be connected to ground		
10	20	I	Torque DAC current scalar	Scales the current from 100% to 12.5% in 12.5% steps; tri-level pin		
<b>I1</b>	21	I	Torque DAC current scalar	Scales the current from 100% to 12.5% in 12.5% steps, th-level pin		
MO	8	I	Microstepping mode setting	Controls step mode (full, half, up to 1/32-step) and single- or dual-		
M1	9	I	pins	edge clocking; tri-level pin		
NC	16	_	No connect	Unused pin not connected internally		
nENBL	11	- 1	Enable driver output	Logic low to enable device outputs and internal indexer; logic high to disable; internal pulldown		
nFAULT	7	OD	Fault indication pin	Pulled logic low with fault condition; open-drain output requires external pullup		
nSLEEP	23	ı	Sleep mode input	Logic high to enable device; logic low to enter low-power sleep mode; internal pulldown		
STEP	12	ı	Step input	A rising edge (or rising and falling depending on step mode) advances the indexer one step; internal pulldown		
TOFF_SEL	10	1	Decay mode off time set	Sets the off-time during current chopping; tri-level pin		



### Pin Functions (continued)

PIN I/O			DESCRIPTION			
NAME	NO.	1/0	DESCRIPTION			
VINT	17	_	Internal regulator Internal supply voltage; bypass to GND with 2.2-µF, 6.3-V capacitor			
VM	15	PWR	Power supply	Connect to motor power supply; bypass to GND with a 0.1- and 10- $\mu$ F (minimum) ceramic capacitor rated for VM		
VREF				Voltage on this pin sets the full scale chopping current; short to VINT if not supplying an external reference voltage		

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature referenced with respect to GND (unless otherwise noted)(1)

	MIN	MAX	UNIT
Power supply voltage (VM)	-0.3	20	V
Power supply voltage ramp rate (VM)	0	2	V/µs
Internal regulator voltage (VINT)	-0.3	3.6	V
Analog input pin voltage (VREF)	-0.3	3.6	V
Control pin voltage (nENABLE, STEP, DIR, I0, I1, M0, M1, DEC0, DEC1, TOFF_SEL, nSLEEP, nFAULT, ADEC)	-0.3	7.0	٧
Continuous phase node pin voltage (AOUT1, AOUT2, BOUT1, BOUT2)	-0.3	VM + 0.6	V
Continuous shunt amplifier input pin voltage (AISEN, BISEN) (2)	-0.6	0.6	V
Peak drive current (AOUT1, AOUT2, BOUT1, BOUT2, AISEN, BISEN)	Interna	Illy limited	Α
T <sub>J</sub> Operating junction temperature	-40	150	°C
T <sub>stg</sub> Storage temperature	-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			MAX	UNIT
V	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	±4000	V
V <sub>(ESD)</sub>	discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	±1500	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
VM	Power supply voltage range <sup>(1)</sup>	4	18	V
VREF	Reference rms voltage range (2)	1	3.3	V
$f_{PWM}$	Applied STEP signal	0	250	kHz
I <sub>VINT</sub>	VINT external load current		1	mA
I <sub>FS</sub>	Motor full-scale current per H-bridge (3)	0	1.4	Α
T <sub>A</sub>	Operating ambient temperature	-40	85	°C

Note that R<sub>DS(ON)</sub> increases and maximum output current is reduced at VM supply voltages below 5 V

(2) Operational at VREF between 0 to 1 V, but accuracy is degraded

3) Power dissipation and thermal limits must be observed

<sup>(2)</sup> Transients of ±1 V for less than 25 ns are acceptable.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### 6.4 Thermal Information

		DRV8846	
	THERMAL METRIC <sup>(1)</sup>	RGE (VQFN)	UNIT
		24 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	34	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	36.9	
$R_{\theta JB}$	Junction-to-board thermal resistance	12.5	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.4	C/VV
ΨЈВ	Junction-to-board characterization parameter	12.5	
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	2.5	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 6.5 Electrical Characteristics

 $T_A = 25$ °C, over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER	R SUPPLIES (VM, VINT)					
VM	VM operating voltage		4		18	V
$I_{\text{VM}}$	VM operating supply current	VM = 12 V, excluding winding current, nSLEEP = 1, nENBL = 0 or 1	3.5	4.5	5.5	mA
$I_{VMQ}$	VM sleep mode supply current	VM = 12 V, nSLEEP = 0, nENBL = 0 or 1	0.5	1.2	3	μΑ
t <sub>SLEEP</sub>	Sleep time	nSLEEP = 0 to sleep mode			1	ms
t <sub>WAKE</sub>	Wake time	nSLEEP = 1 to output transition			1	ms
t <sub>ON</sub>	Power-on time	VM > V <sub>UVLO</sub> rising to output transition			1	ms
VINT	VINT voltage	$VM > 4 V$ , $I_{OUT} = 0 A to 1 mA$	3.13	3.3	3.47	V
LOGIC-	LEVEL INPUTS (STEP, DIR, nENBL, n	SLEEP, ADEC)				
$V_{IL}$	Input logic low voltage		0		0.7	V
$V_{IH}$	Input logic high voltage		1.6		5.5	V
$V_{HYS}$	Input logic hysteresis			100		mV
I <sub>IL</sub>	Input logic low current	VIN = 0 V	-1		1	μΑ
I <sub>IH</sub>	Input logic high current	VIN = 5 V	1		30	μΑ
D	Pulldown resistance	nENBL, STEP, DIR, ADEC		200		kΩ
R <sub>PD</sub>	Fulldown resistance	nSLEEP		500		K12
$t_{DEG}$	Input deglitch time			200		ns
t <sub>PROP</sub>	Propagation delay	STEP edge to current change		600		ns
TRI-LEV	VEL INPUTS (I0, I1, M0, M1, DEC0, DEC	C1, TOFF_SEL)				
$V_{IL}$	Tri-level input logic low voltage		0		0.7	V
$V_{IZ}$	Tri-level input Hi-Z voltage			1.1		V
$V_{IH}$	Tri-level input logic high voltage		1.6		5.5	V
$V_{HYS}$	Tri-level input hysteresis		100			mV
$I_{\rm IL}$	Tri-level input logic low current	$V_{IN} = 0 V$	-30		-1	μΑ
I <sub>IH</sub>	Tri-level input logic high current	$V_{IN} = 5 V$	1		30	μΑ
$R_{PD}$	Tri-level pulldown resistance	To GND		170		kΩ
$R_{PU}$	Tri-level pullup resistance	To VINT		340		kΩ
CONTR	OL OUTPUTS (nFAULT)					
$V_{OL}$	Output logic low voltage	$I_O = 5 \text{ mA}$			0.5	V
I <sub>OH</sub>	Output logic high leakage	V <sub>O</sub> = 3.3 V	-1		1	μΑ



## **Electrical Characteristics (continued)**

T<sub>A</sub> = 25°C, over recommended operating conditions unless otherwise noted

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
MOTOR	DRIVER OUTPUTS (AOUT1, AOUT2, BO	UT1, BOUT2)				
Б	High side FFT as variations	VM = 12 V, I = 0.5 A, T <sub>J</sub> = 25°C		550		0
R <sub>DS(ON)</sub>	High-side FET on resistance	$VM = 12 V, I = 0.5 A, T_J = 85^{\circ}C^{(1)}$		660		mΩ
<b>D</b>	Lavorida EET an accidence	VM = 12 V, I = 0.5 A, T <sub>J</sub> = 25°C		350		0
R <sub>DS(ON)</sub>	Low-side FET on resistance	$VM = 12 V, I = 0.5 A, T_J = 85^{\circ}C^{(1)}$		420		mΩ
I <sub>OFF</sub>	Off-state leakage current	VM = 5 V, T <sub>J</sub> = 25°C	-1		1	μΑ
t <sub>RISE</sub>	Output rise time			60		ns
t <sub>FALL</sub>	Output fall time			60		ns
t <sub>DEAD</sub>	Output dead time	Internal dead time		200		ns
PWM CU	IRRENT CONTROL (VREF, AISEN, BISEI	v)				
I <sub>REF</sub>	Externally applied VREF input current	VREF = 1 to 3.3 V			1	μΑ
V <sub>TRIP</sub>	xISEN trip voltage	For 100% current step with VREF = 3.3 V		500		mV
A <sub>ISENSE</sub>	Current sense amplifer gain	Reference only		6.6		V/V
		TOFF_SEL = GND		20		
t <sub>OFF</sub>	Current control constant off time	TOFF_SEL = Hi-Z		10		μS
		TOFF_SEL = VINT		30		
PROTEC	TION CIRCUITS					
	VMA condemonate and landered	VM falling; UVLO report			2.9	V
$V_{UVLO}$	VM undervoltage lockout	VM rising; UVLO recovery			3	V
I <sub>OCP</sub>	Overcurrent protection trip level		2			Α
t <sub>OCP</sub>	Overcurrent deglitch time			2.8		μS
t <sub>RETRY</sub>	Overcurrent protection period			1.6		ms
T <sub>TSD</sub>	Thermal shutdown temperature	Die temperature T <sub>J</sub>	150	160	180	°C
T <sub>HYS</sub>	Thermal shutdown hysteresis	Die temperature T <sub>J</sub>		50		°C

<sup>(1)</sup> Not tested in production; limits are based on characterization data

## 6.6 Timing Requirements

 $T_A = 25^{\circ}C$ , over recommended operating conditions unless otherwise noted

NO.			MIN	MAX	UNIT
1	$f_{STEP}$	Step frequency		250	kHz
2	t <sub>WH(STEP)</sub>	Pulse duration, STEP high	1.9		μS
3	t <sub>WL(STEP)</sub>	Pulse duration, STEP low	1.9		μS
4	t <sub>SU(STEP)</sub>	Setup time, DIR or Mx to STEP rising	200		ns
5	t <sub>H(STEP)</sub>	Hold time, DIR or Mx to STEP rising	200		ns

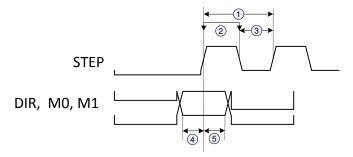


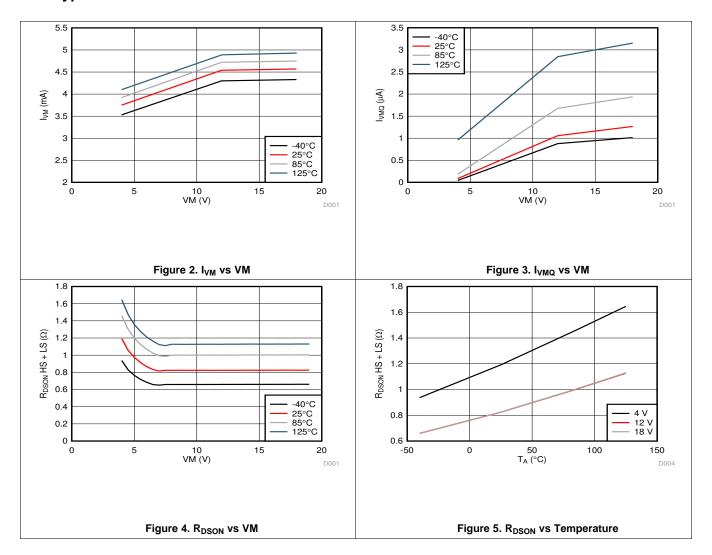
Figure 1. Timing Diagram

Product Folder Links: DRV8846

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# 6.7 Typical Characteristics





### 7 Detailed Description

#### 7.1 Overview

The DRV8846 is an integrated motor driver solution for bipolar stepper motors. The device integrates 2 H-bridges that use NMOS low-side drivers and PMOS high-side drivers, current sense regulation circuitry, and a microstepping indexer. The DRV8846 can be powered with a supply range between 4 to 18 V and is capable of providing an output current to 1.4-A full scale per H-bridge.

A simple STEP/DIR interface allows easy interfacing to the controller circuit. The internal indexer is able to execute high-accuracy microstepping without requiring the processor to control the current level.

The PWM off-time,  $t_{OFF}$  can be adjusted to 10, 20, or 30  $\mu s$ .

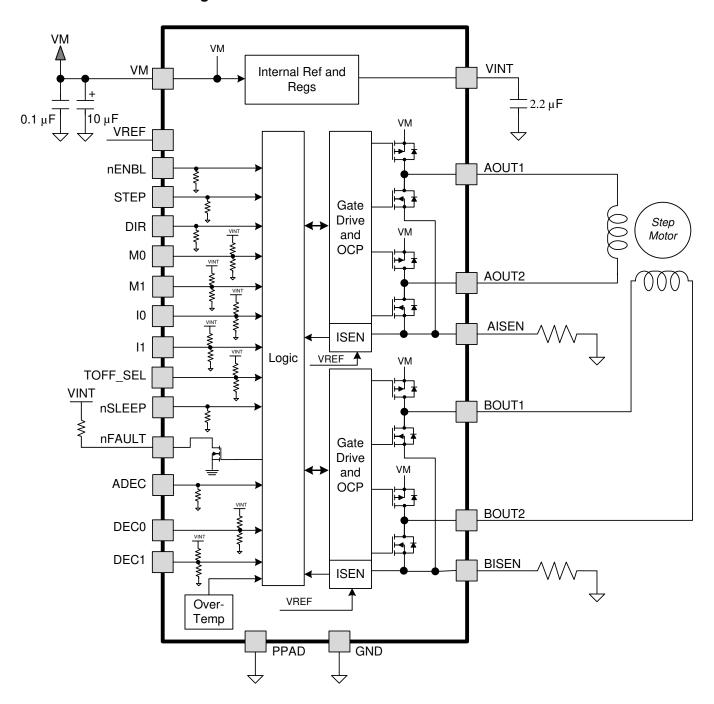
The DRV8846 has an smart tune feature that automatically adjusts the decay setting to minimize current ripple while still reacting quickly to step changes. This feature allows the DRV8846 to quickly be integrated into a system.

A torque DAC feature allows the controller to scale the output current without needing to scale the analog reference voltage input VREF. The torque DAC is accessed using digital input pins. This allows the controller to save power by decreasing the current consumption when not required.

A low-power sleep mode is included, which allows the system to save power when not driving the motor.



## 7.2 Functional Block Diagram





### 7.3 Feature Description

Table 1 lists the recommended external components for the device.

**Table 1. External Components** 

COMPONENT	PIN 1	PIN 2	RECOMMENDED		
C <sub>VM</sub>	VM	GND	10-μF (minimum) ceramic capacitor rated for VM		
$C_VM$	VM	GND	0.1-µF ceramic capacitor rated for VM		
C <sub>VINT</sub>	VINT	GND	6.3-V, 2.2-µF ceramic capacitor		
R <sub>nFAULT</sub>	VCC <sup>(1)</sup>	nFAULT	>5 kΩ		
R <sub>AISEN</sub>	AISEN	GND	Sense resistor, see applications section for sizing		
R <sub>BISEN</sub>	BISEN	GND	Sense resistor, see applications section for sizing		

<sup>(1)</sup> VCC is not a pin on the DRV8846, but a VCC supply voltage pullup is required for open-drain output nFAULT; nFAULT may be pulled up to VINT through a resistor R<sub>nFAULT</sub>

#### 7.3.1 PWM Motor Drivers

DRV8846 contains two identical H-bridge motor drivers with current-control PWM circuitry. Figure 6 shows a block diagram of the circuitry.

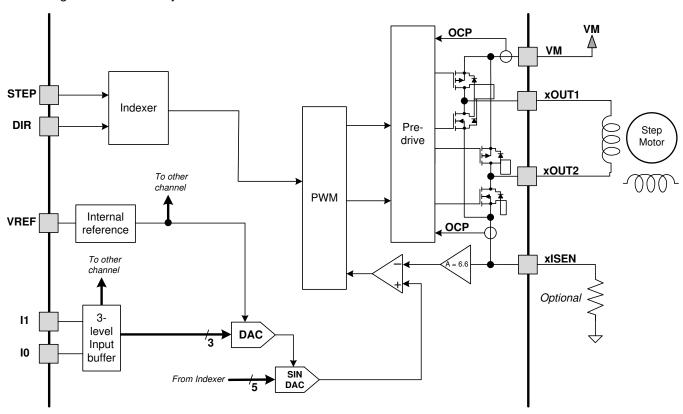


Figure 6. PWM Motor Driver Circuitry

### 7.3.2 Micro-Stepping Indexer

To allow a simple step and direction interface to control stepper motors, the DRV8846 contains a microstepping indexer. The indexer controls the state of the H-bridges automatically. When the correct transition is applied at the STEP input, the indexer moves to the next step, according to the direction set by the DIR pin. In 1/8, 1/16, and 1/32 step modes, both the rising and falling edges of the STEP input may be used to advance the indexer, depending on the M0 / M1 setting.

The nENBL pin disables the output stage in indexer mode. When nENBL = 1, the indexer inputs are still active and respond to the STEP and DIR input pins; only the output stage is disabled.



The indexer logic in the DRV8846 allows a number of different stepping configurations. The M0 and M1 pins configure the stepping format (see Table 2).

**Table 2. Step Mode Settings** 

M1	МО	STEP MODE
0	0	Full step (2-phase excitation), rising-edge only
0	Z	1/2 step (1-2 phase excitation), rising-edge only
0	1	1/4 step (W1-2 phase excitation), rising-edge only
Z	0	8 microsteps/step, rising-edge only
Z	Z	8 microsteps/step, rising and falling edges
Z	1	16 microsteps/step, rising-edge only
1	0	16 microsteps/step, rising and falling edges
1	Z	32 microsteps/step, rising-edge only
1	1	32 microsteps/step, rising and falling edges

Note that the M0 and M1 pins are tri-level inputs. These pins can be driven logic low, logic high, or high-impedance (Z), like the I0 and I1 pins described previously.

For 1/8, 1/16, and 1/32-step modes, selections are available to advance the indexer only on the rising edge of the STEP input, or on both the rising and falling edges.

The step mode may be changed on-the-fly while the motor is moving. The indexer advances to the next valid state for the new M0 / M1 setting at the next rising edge of STEP.

The home state is 45°. The indexer enters the home state after power-up, after exiting UVLO, or after exiting sleep mode (see the yellow-shaded cells in Table 3 also indicated with a table note).

Table 3 shows the relative current and step directions for different step mode settings. At each rising edge of the STEP input, the indexer travels to the next state in the table. The direction is shown with the DIR pin high; if the DIR pin is low, the sequence is reversed. Positive current is defined as xOUT1 = positive with respect to xOUT2.

**Table 3. Relative Current and Step Directions** 

1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
1	1	1	1	1		100%	0%	0
2						100%	5%	3
3	2					100%	10%	6
4						99%	15%	8
5	3	2				98%	20%	11
6						97%	24%	14
7	4					96%	29%	17
8						94%	34%	20
9	5	3	2			92%	38%	23
10						90%	43%	25
11	6					88%	47%	28
12						86%	51%	31
13	7	4				83%	56%	34
14						80%	60%	37
15	8					77%	63%	39
16						74%	67%	42
17 <sup>(1)</sup>	9 <sup>(1)</sup>	5 <sup>(1)</sup>	3 <sup>(1)</sup>	2 <sup>(1)</sup>	1 <sup>(1)</sup>	71%	71%	45
18						67%	74%	48
19	10					63%	77%	51
20						60%	80%	53

(1) The indexer enters the home state after power-up, after exiting UVLO, or after exiting sleep mode.



# Table 3. Relative Current and Step Directions (continued)

					p = c c c c			
1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
21	11	6				56%	83%	56
22						51%	86%	59
23	12					47%	88%	62
24						43%	90%	65
25	13	7	4			38%	92%	68
26						34%	94%	70
27	14					29%	96%	73
28						24%	97%	76
29	15	8				20%	98%	79
30						15%	99%	82
31	16					10%	100%	84
32						5%	100%	87
33	17	9	5	3		0%	100%	90
34						-5%	100%	93
35	18					-10%	100%	96
36						-15%	99%	98
37	19	10				-20%	98%	101
38						-24%	97%	104
39	20					-29%	96%	107
40						-34%	94%	110
41	21	11	6			-38%	92%	113
42						-43%	90%	115
43	22					-47%	88%	118
44						-51%	86%	121
45	23	12				-56%	83%	124
46						-60%	80%	127
47	24					-63%	77%	129
48						-67%	74%	132
49	25	13	7	4	2	-71%	71%	135
50					_	-74%	67%	138
51	26					-77%	63%	141
52						-80%	60%	143
53	27	14				-83%	56%	146
54						-86%	51%	149
55	28					-88%	47%	152
56						-90%	43%	155
57	29	15	8			-92%	38%	158
58	20	10	J			-94%	34%	160
59	30					-96%	29%	163
60	30					-97%	24%	166
61	31	16				-98%	20%	169
62	01	10				-99%	15%	172
63	32					-99 <i>%</i> -100%	10%	174
64	32					-100% -100%	5%	174
65	33	17	9	5		-100% -100%	0%	180
66	33	17	3	3		-100% -100%	-5%	183
67	34					-100% -100%	-5% -10%	186
07	34					-100%	-10%	100

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# Table 3. Relative Current and Step Directions (continued)

					p Directions		,	
1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
68						-99%	-15%	188
69	35	18				-98%	-20%	191
70						-97%	-24%	194
71	36					-96%	-29%	197
72						-94%	-34%	200
73	37	19	10			-92%	-38%	203
74						-90%	-43%	205
75	38					-88%	-47%	208
76						-86%	-51%	211
77	39	20				-83%	-56%	214
78						-80%	-60%	217
79	40					-77%	-63%	219
80						-74%	-67%	222
81	41	21	11	6	3	-71%	-71%	225
82						-67%	-74%	228
83	42					-63%	-77%	231
84						-60%	-80%	233
85	43	22				-56%	-83%	236
86						-51%	-86%	239
87	44					-47%	-88%	242
88						-43%	-90%	245
89	45	23	12			-38%	-92%	248
90						-34%	-94%	250
91	46					-29%	-96%	253
92	.0					-24%	-97%	256
93	47	24				-20%	-98%	259
94						-15%	-99%	262
95	48					-10%	-100%	264
96	40					-5%	-100%	267
97	49	25	13	7		0%	-100%	270
98	40	20	10	,		5%	-100%	273
99	50					10%	-100%	276
100	00					15%	-99%	278
101	51	26				20%	-98%	281
102	01	20				24%	-97%	284
103	52					29%	-96%	287
104						34%	-94%	290
105	53	27	14			38%	-92%	293
106	33	<u>-1</u>	17			43%	-92 <i>%</i> -90%	295
107	54					47%	-90 % -88%	293
108	JT					51%	-86%	301
109	55	28				56%	-83%	304
110	33	20				60%	-80%	307
111	56					63%		307
	OC						-77%	
112	E7	20	15	0	4	67%	-74%	312
113	57	29	15	8	4	71% 74%	-71% -67%	315 318

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Table 3. Relative Current and Step Directions (continued)

1/32 STEP	1/16 STEP	1/8 STEP	1/4 STEP	1/2 STEP	FULL STEP 70%	WINDING CURRENT A	WINDING CURRENT B	ELECTRICAL ANGLE
115	58					77%	-63%	321
116						80%	-60%	323
117	59	30				83%	-56%	326
118						86%	<b>-</b> 51%	329
119	60					88%	-47%	332
120						90%	-43%	335
121	61	31	16			92%	-38%	338
122						94%	-34%	340
123	62					96%	-29%	343
124						97%	-24%	346
125	63	32				98%	-20%	349
126						99%	-15%	352
127	64					100%	-10%	354
128						100%	-5%	357

### 7.3.3 Current Regulation

The current through the motor windings is regulated by an adjustable fixed-off-time PWM current regulation circuit. When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage, inductance of the winding, and the magnitude of the back EMF present. After the current reaches the current chopping threshold, the bridge enters a decay mode for a fixed period of time to decrease the current, which is configurable between 10 to 30 µs through the tri-level input TOFF\_SEL. After the time expires, the bridge is reenabled, starting another PWM cycle.

**Table 4. Fixed Off-Time Selection** 

TOFF_SEL	TOFF Duration
0	20 μs
Z	10 μs
1	30 μs

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the xISEN pin, with a reference voltage. The reference voltage can be supplied by an internal reference of 3.3 V (which requires VINT to be connected to VREF), or externally supplied to the VREF pin. The reference voltage is then scaled first by the 3-bit torque DAC, then by the output of a sine lookup table that is applied to a sine-weighted DAC (sine DAC). The voltage is attenuated by a factor of 6.6.

The full-scale (100%) chopping current is calculated as follows:

$$I_{FS} = \frac{VREF}{6.6 \times R_{ISENSE}} \times TORQUE$$

where

- I<sub>FS</sub> is the full scale regulated current
- · VREF is the voltage on the VREF pin
- R<sub>ISENSE</sub> is the resistance of the sense resistor
- TORQUE is the scaling percentage from the torque DAC.

Example: Using VREF is 3.3 V, torque DAC = 100%, and a 500-m $\Omega$  sense resistor, the full-scale chopping current is 3.3 V / (6.6 × 500 m $\Omega$ ) × 100% = 1 A.

The current for both motor windings is scaled depending on the I0 and I1 pins, which drive a 3-bit linear DAC, as in Table 5.

Product Folder Links: DRV8846

(1)



**Table 5. Torque DAC Settings** 

l1	10	CURRENT SCALING (TORQUE)
0	0	100%
0	Z	87.5%
0	1	75%
Z	0	62.5%
Z	Z	50%
Z	1	37.5%
1	0	25%
1	Z	12.5%
1	1	0% (outputs disabled)

Table 6 gives the xISEN trip voltage at a given DAC code and I[1:0] setting.

Table 6. Torque DAC xISENS Trip Levels (VREF = 3.3 V)

Sine DAC	Torque DAC I[1:0] Setting								
Code	00 - 100%	0Z - 87.5%	01 - 75%	Z0 - 62.5%	ZZ - 50%	Z1 - 37.5%	10 - 25%	1Z - 12.5%	
31	500 mV	438 mV	375 mV	313 mV	250 mV	188 mV	125 mV	63 mV	
30	500 mV	438 mV	375 mV	313 mV	250 mV	188 mV	125 mV	63 mV	
29	495 mV	433 mV	371 mV	309 mV	248 mV	186 mV	124 mV	62 mV	
28	490 mV	429 mV	368 mV	306 mV	245 mV	184 mV	123 mV	61 mV	
27	485 mV	424 mV	364 mV	303 mV	243 mV	182 mV	121 mV	61 mV	
26	480 mV	420 mV	360 mV	300 mV	240 mV	180 mV	120 mV	60 mV	
25	470 mV	411 mV	353 mV	294 mV	235 mV	176 mV	118 mV	59 mV	
24	460 mV	403 mV	345 mV	288 mV	230 mV	173 mV	115 mV	58 mV	
23	450 mV	394 mV	338 mV	281 mV	225 mV	169 mV	113 mV	56 mV	
22	440 mV	385 mV	330 mV	275 mV	220 mV	165 mV	110 mV	55 mV	
21	430 mV	376 mV	323 mV	269 mV	215 mV	161 mV	108 mV	54 mV	
20	415 mV	363 mV	311 mV	259 mV	208 mV	156 mV	104 mV	52 mV	
19	400 mV	350 mV	300 mV	250 mV	200 mV	150 mV	100 mV	50 mV	
18	385 mV	337 mV	289 mV	241 mV	193 mV	144 mV	96 mV	48 mV	
17	370 mV	324 mV	278 mV	231 mV	185 mV	139 mV	93 mV	46 mV	
16	355 mV	311 mV	266 mV	222 mV	178 mV	133 mV	89 mV	44 mV	
15	335 mV	293 mV	251 mV	209 mV	168 mV	126 mV	84 mV	42 mV	
14	315 mV	276 mV	236 mV	197 mV	158 mV	118 mV	79 mV	39 mV	
13	300 mV	263 mV	225 mV	188 mV	150 mV	113 mV	75 mV	38 mV	
12	280 mV	245 mV	210 mV	175 mV	140 mV	105 mV	70 mV	35 mV	
11	255 mV	223 mV	191 mV	159 mV	128 mV	96 mV	64 mV	32 mV	
10	235 mV	206 mV	176 mV	147 mV	118 mV	88 mV	59 mV	29 mV	
9	215 mV	188 mV	161 mV	134 mV	108 mV	81 mV	54 mV	27 mV	
8	190 mV	166 mV	143 mV	119 mV	95 mV	71 mV	48 mV	24 mV	
7	170 mV	149 mV	128 mV	106 mV	85 mV	64 mV	43 mV	21 mV	
6	145 mV	127 mV	109 mV	91 mV	73 mV	54 mV	36 mV	18 mV	
5	120 mV	105 mV	90 mV	75 mV	60 mV	45 mV	30 mV	15 mV	
4	100 mV	88 mV	75 mV	63 mV	50 mV	38 mV	25 mV	13 mV	
3	75 mV	66 mV	56 mV	47 mV	38 mV	28 mV	19 mV	9 mV	
2	50 mV	44 mV	38 mV	31 mV	25 mV	19 mV	13 mV	6 mV	
1	25 mV	22 mV	19 mV	16 mV	13 mV	9 mV	6 mV	3 mV	
0	0 mV	0 mV	0 mV	0 mV	0 mV	0 mV	0 mV	0 mV	



### 7.3.4 Decay Mode

After the chopping current threshold is reached, the drive current is interrupted, but due to the inductive nature of the motor, current must continue to flow for some period of time (called recirculation current). To handle this recirculation current, the H-bridge can operate in two different states, fast decay or slow decay (or a mixture of fast and slow decay).

In fast-decay mode, after the PWM chopping current level is reached, the H-bridge reverses state to allow winding current to flow through the opposing FETs. As the winding current approaches 0, the bridge is disabled to prevent any reverse current flow. For fast-decay mode, see number 2 in Figure 7.

In slow-decay mode, winding current is recirculated by enabling both of the low-side FETs in the bridge. For slow-decay mode, see number 3 in Figure 7.

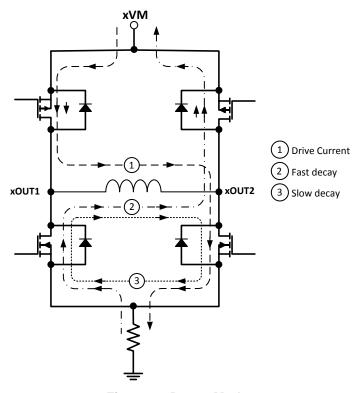


Figure 7. Decay Modes

The DRV8846 supports fast, slow, mixed, and smart tune modes. With stepper motors, the decay mode is chosen for a given stepper motor and operating conditions to minimize mechanical noise and vibration.

In mixed decay mode, the current recirculation begins as fast decay, but at a fixed period of time (determined by the state of the DEC1 and DEC0 pins shown in Table 7) the current recirculation switches to slow decay mode for the remainder of the fixed PWM period. Note that the DEC1 and DEC0 pins are tri-level inputs; these pins can be driven logic low, logic high, or high-impedance (Z).

Figure 8 shows the current waveforms in slow, fast, and 25% and 1 t<sub>BLANK</sub> mixed decay modes.



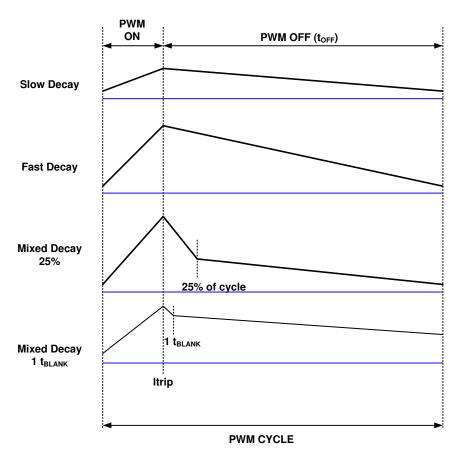


Figure 8. Decay Behavior

**Table 7. Decay Pins Configuration** 

DEC1	DEC0	Decay Mode (Increasing Current)	Decay Mode (Decreasing Current)
0	0	Slow decay	Slow decay
0	Z	Slow decay	Mixed decay: 25% fast
0	1	Slow decay	Mixed decay: 1 t <sub>BLANK</sub>
Z	0	Mixed decay: 1 t <sub>BLANK</sub>	Mixed decay: 1 t <sub>BLANK</sub>
Z	Z	Mixed decay: 50% fast	Mixed decay: 50% fast
Z	1	Mixed decay: 25% fast	Mixed decay: 25% fast
1	0	Slow decay	Mixed decay: 50% fast
1	Z	Slow decay	Mixed decay: 12.5% fast
1	1	Slow decay	Fast decay

Figure 9 shows increasing and decreasing current. When current is decreasing, the decay mode used is fast, slow, or mixed as commanded by the DEC1 and DEC0 pins. Three DEC pin selections allow for mixed decay during increasing current.

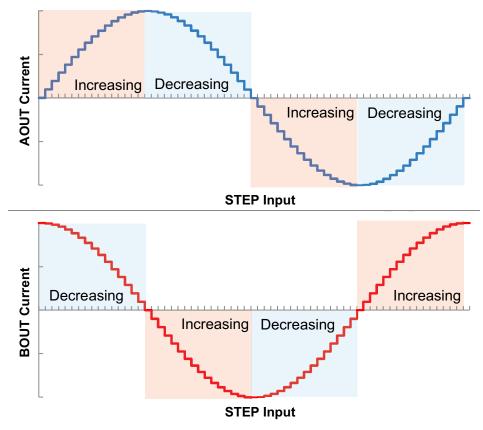


Figure 9. Increasing and Decreasing Current

Smart tune mode simplifies the decay mode selection by dynamically changing to adjust for current level, step change, supply variation, BEMF, and load. To enable smart tune mode, pull the ADEC pin to logic high and pull DEC0 and DEC1 pins to logic high. The state of the ADEC pin is only evaluated when exiting sleep mode. (ADEC pin must be high before exiting sleep to enable smart tune mode.)

Smart tune adjusts the time spent in fast decay to minimize current ripple and quickly adjust to current-step changes. If the drive time is longer than the minimum ( $t_{BLANK}$ ), in order to reach the current trip point, the decay mode applied is slow decay (see Figure 10).

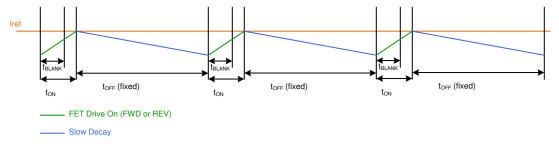


Figure 10. Smart Tune - Slow Decay Operation

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When the minimum drive time ( $t_{BLANK}$ ) provides more current than the regulation point, fast decay of 1-  $t_{BLANK}$  is applied. If the second drive period also provides more current than the regulation point, fast decay of 2  $t_{BLANK}$  is applied. If a third (or more) consecutive period provides more current than the regulation point, fast decay using 25% of  $t_{OFF}$  time is applied. When the minimum drive time is insufficient to reach the current regulation level, slow decay is applied until the current exceeds the current reference level (see Figure 11).

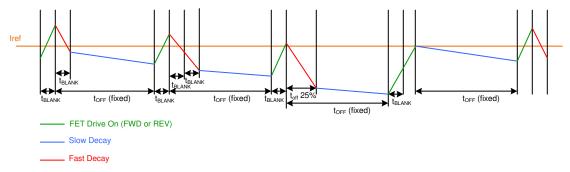


Figure 11. Smart Tune - Mixed Decay Operation

Figure 12 shows a case for smart tune where a step occurs. The system starts with 1  $t_{BLANK}$  of fast decay and works up to 25% of  $t_{OFF}$  time for fast decay until the current is regulated again.

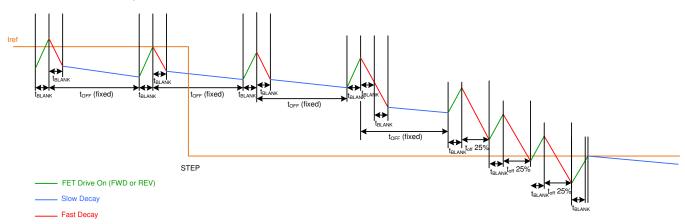


Figure 12. Smart Tune – Step Operation

### 7.3.5 Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a period of time before enabling the current sense circuitry. Note that the blanking time also sets the minimum drive time of the PWM.

The time,  $t_{BLANK}$ , is determined by the sine DAC code and the torque DAC setting. The timing information for  $t_{BLANK}$  is given in Table 8.



### Table 8. t<sub>BLANK</sub> Settings

	Table 8. t <sub>BLANK</sub> Settings									
Sine DAC				Torque DAC	I[1:0] Setting					
Code	00 - 100%	0Z - 87.5%	01 - 75%	Z0 - 62.5%	ZZ - 50%	Z1 - 37.5%	10 - 25%	1Z - 12.5%		
31	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
30	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
29	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
28	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
27	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
26	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
25	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
24	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
23	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
22	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
21	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
20	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
19	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
18	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
17	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
16	1.80 µs	1.80 µs	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	0.90 µs		
15	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
14	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
13	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
12	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
11	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
10	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
9	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
8	1.50 µs	1.50 µs	1.50 µs	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs		
7	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
6	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
5	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
4	1.20 µs	1.20 µs	1.20 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
3	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
2	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
1	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		
0	0.90 µs	0.90 μs	0.90 µs	0.90 μs	0.90 µs	0.90 µs	0.90 µs	0.90 µs		

### 7.3.6 Protection Circuits

The DRV8846 is fully protected against undervoltage, overcurrent, and overtemperature events.

### 7.3.6.1 Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by limiting the gate drive. If this analog current limit persists for longer than the OCP deglitch time  $t_{\text{OCP}}$ , all FETs in the H-bridge are disabled and the nFAULT pin is driven low. The device remains disabled until the retry time,  $t_{\text{RETRY}}$ , occurs. The OCP is independent for each H-bridge.

Overcurrent conditions are detected independently on both high-side and low-side devices; that is, a short to ground, supply, or across the motor winding all result in an OCP event. Note that OCP does not use the current sense circuitry used for PWM current control, so OCP functions without the presence of the xISEN resistors.



#### 7.3.6.2 Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge are disabled and the nFAULT pin is driven low. After the die temperature falls to a safe level, operation automatically resumes. The nFAULT pin is released after operation has resumed.

#### 7.3.6.3 Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pin falls below the UVLO falling threshold voltage,  $V_{UVLO}$ , all circuitry in the device is disabled, and all internal logic is reset. Operation resumes when VM rises above the UVLO rising threshold. The nFAULT pin is driven low during an undervoltage condition and is released after operation has resumed.

**Table 9. Fault Behavior** 

Fault	Error Report	H-Bridge	Internal Circuits	Recovery
VM UVLO	nFAULT unlatched	Disabled	Shut down	System and fault clears on recovery
ОСР	nFAULT unlatched	Disabled	Operating	System and fault clears on recovery and motor is driven after time, t <sub>RETRY</sub>
TSD	nFAULT unlatched	Disabled	Operating	System and fault clears on recovery

#### 7.4 Device Functional Modes

The DRV8846 device is active unless the nSLEEP pin is driven low. In sleep mode, the VINT regulator is disabled and the H-bridge FETs are disabled (Hi-Z). The time  $t_{SLEEP}$  must elapse after a falling edge on the nSLEEP pin before the device enters sleep mode. The DRV8846 is brought out of sleep mode by bringing the nSLEEP pin high. The time  $t_{WAKE}$  must elapse, after nSLEEP is brought high, before the outputs change state.

If the nENBL pin is brought high, the H-bridge outputs are disabled, but the internal logic is still active. An appropriate edge on STEP (depending on the step mode) advances the indexer, but the outputs do not change state until nENBL is driven low.

**Table 10. Operating Modes** 

Mode	Condition	H-Bridge	VINT	Indexer
Operating	4 V < VM < 18 V nSLEEP pin = 1 nENBL = 0	Operating	Operating	Operating
Disabled	4 V < VM < 18 V nSLEEP pin = 1 nENBL = 1	Disabled	Operating	Operating
Sleep	4 V < VM < 18 V nSLEEP pin = 0	Disabled	Disabled	Disabled
Fault	Any fault condition met	Disabled	Depends on fault	Depends on fault



### 8 Application and Implementation

#### **NOTE**

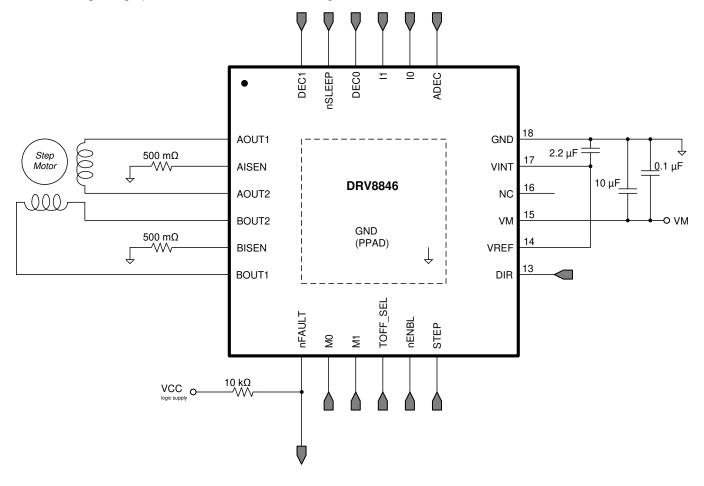
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The DRV8846 is used in stepper motor control.

### 8.2 Typical Application

The following design procedure can be used to configure the DRV8846.





### **Typical Application (continued)**

#### 8.2.1 Design Requirements

Table 11 gives design input parameters for system design.

**Table 11. System Design Input Parameters** 

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Nominal supply voltage	VM	12 V
Supply voltage range	VIVI	4 to 18 V
Motor winding resistance	$R_{L}$	3.0 Ω/phase
Motor winding inductance	LL	330 μH/phase
Motor full step angle	$\theta_{\sf step}$	1.8°/step
Target stepping level	nm	1/8 step
Target motor speed	V	400 rpm
Target chopping current	I <sub>CHOP</sub>	500 mA
Chopping current reference voltage	VREF	3.3 V
Current scaling	TORQUE	100%

#### 8.2.2 Detailed Design Procedure

#### 8.2.2.1 Stepper Motor Speed

The first step in configuring the DRV8846 requires the desired motor speed and stepping level. The DRV8846 can support from full step to 1/32 step mode.

If the target motor speed is too high, the motor will not spin. Make sure that the motor can support the target speed.

For a desired motor speed (v), microstepping level (nm), and motor full step angle ( $\theta_{step}$ ),

$$f_{\text{step}} \text{ (steps/s)} = \frac{v(\text{rpm}) \times n_{\text{m}}(\text{steps}) \times 6}{\theta_{\text{step}} (^{\circ}/\text{step})}$$
(2)

 $\theta_{\text{step}}$  can be found in the stepper motor data sheet or often written on the motor itself.

For DRV8846, the microstepping levels are set by the M0/M1 pins and can be any of the settings in Table 2. Higher microstepping means a smoother motor motion and less audible noise, but increases the switching losses and requires a higher  $f_{\text{step}}$  to achieve the same motor speed.

#### 8.2.2.2 Current Regulation

The chopping current ( $I_{CHOP}$ ) is the maximum current driven through either winding. This quantity will depend on the sense resistor value ( $R_{XISEN}$ ).

$$I_{CHOP} = \frac{VREF}{6.6 \times R_{ISENSE}} \times TORQUE$$
(3)

 $I_{CHOP}$  is set by a comparator which compares the voltage across  $R_{XISEN}$  to a reference voltage. Note that  $I_{CHOP}$  must follow Equation 4 to avoid saturating the motor.

$$I_{CHOP}\left(A\right) \\ < \frac{VM\left(V\right)}{R_{L}\left(\Omega\right) + 2 \times R_{DS(ON)}\left(\Omega\right) + R_{SENSE}\left(\Omega\right)}$$

where

- · VM is the motor supply voltage.
- R<sub>L</sub> is the motor winding resistance.

(4)

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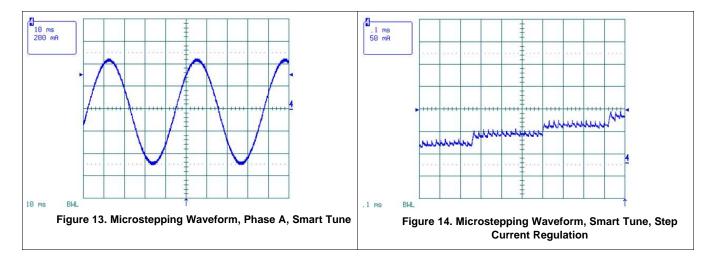


#### 8.2.2.3 Decay Modes

The DRV8846 supports four different decay modes: slow decay, fast decay, mixed decay, and smart tune. The first selection to try is the smart tune mode, which adjusts the decay mode automatically to improve current regulation. The current through the motor windings is regulated using a fixed-off-time PWM scheme. This means that after any drive phase, when a motor has reached the current chopping threshold (I<sub>CHOP</sub>), the DRV8846 places the motor in one of the four decay modes until the PWM cycle has expired. Afterward, a new drive phase starts.

The blanking time, t<sub>BLANK</sub>, defines the minimum drive time for the current chopping. I<sub>CHOP</sub> is ignored during t<sub>BLANK</sub>, so the winding current may overshoot the trip level during this blanking period.

#### 8.2.3 Application Curves



Product Folder Links: DRV8846

binii Documentation Feedback

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### 9 Power Supply Recommendations

The DRV8846 is designed to operate from an input voltage supply (VM) range between 4 and 18 V. A 0.1- $\mu$ F ceramic capacitor rated for VM must be placed as close to the DRV8846 as possible. In addition, a bulk 10- $\mu$ F capacitor must be included on VM.

### 10 Layout

### 10.1 Layout Guidelines

The VM terminal should be bypassed to GND using a low-ESR ceramic bypass capacitor with a recommended value of 10  $\mu$ F rated for VM. This capacitor should be placed as close to the VM pin as possible with a thick trace or ground plane connection to the device GND pin.

Bypass VINT to ground with a ceramic capacitor rated 6.3 V. Place this bypassing capacitor as close to the pin as possible.

### 10.2 Layout Example

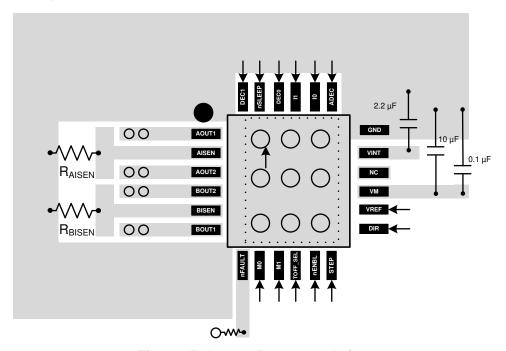


Figure 15. Layout Recommendation



### 11 Device and Documentation Support

### 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation see the following:

- Achieving Changeable Holding Current of a DRV88x Stepper Motor Driver
- DRV8846 Evaluation Module

### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 11.3 Community Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 11.4 Trademarks

E2E is a trademark of Texas Instruments.

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### 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### PACKAGE OPTION ADDENDUM

6-Feb-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
DRV8846RGER	ACTIVE	VQFN	RGE	24	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8846	Samples
DRV8846RGET	ACTIVE	VQFN	RGE	24	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-3-260C-168 HR	-40 to 85	DRV8846	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.





6-Feb-2020

**PACKAGE MATERIALS INFORMATION** 

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8846RGER	VQFN	RGE	24	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
DRV8846RGET	VQFN	RGE	24	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8846RGER	VQFN	RGE	24	3000	367.0	367.0	35.0
DRV8846RGET	VQFN	RGE	24	250	210.0	185.0	35.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4204104/H







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.





NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.





NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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